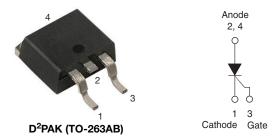
Vishay Semiconductors

# **Thyristor Surface Mount, Phase Control SCR, 8 A**



8 A

800 V

1.2 V

15 mA

-40 to +125 °C

D<sup>2</sup>PAK (TO-263AB)

Single SCR

**PRIMARY CHARACTERISTICS** 

I<sub>T(AV)</sub>

V<sub>DRM</sub>/V<sub>RRM</sub>

V<sub>TM</sub>

ТJ

Package

Circuit configuration

www.vishay.com

FEATURES
----------

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

### DESCRIPTION

The VS-12TTS08SLHM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55 \text{ °C}$ , $T_J = 125 \text{ °C}$ , common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I <sub>T(AV)</sub>	Sinusoidal waveform	8	Α				
I <sub>T(RMS)</sub>		12.5	A				
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V				
I <sub>TSM</sub>		110	A				
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V				
dV/dt		150	V/µs				
dl/dt		100	A/µs				
TJ	Range	-40 to +125	°C				

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 125 °C mA					
VS-12TTS08SLHM3	800	800	5.0					

Revision: 22-Feb-18 1 Document Number: 96121 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT HALOGEN

## VS-12TTS08SLHM3



www.vishay.com

## Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 108 °C, 180° conduction, half sine wave	8				
Maximum RMS on-state current	I <sub>T(RMS)</sub>	$T_{\rm C} = 100$ C, 100 conduction, that sine wave	12.5				
Maximum peak one-cycle	<b>L</b>	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	95	A			
non-repetitive surge current	ITSM	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	110				
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{RRM}$ applied, $T_J$ = 125 °C	45	A <sup>2</sup> s			
Maximum - tior fusing	1-1	10 ms sine pulse, no voltage reapplied, $T_J$ = 125 °C	64	A-S			
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied, $T_{J}$ = 125 $^{\circ}\text{C}$	640	A²√s			
Maximum on-state voltage drop	V <sub>TM</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V			
On-state slope resistance	r <sub>t</sub>	T_I = 125 °C		mΩ			
Threshold voltage	V <sub>T(TO)</sub>	1) = 125 0	0.87	V			
Maximum reverse and direct leakage current	1/1	$T_J = 25 \text{ °C}$	0.05				
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	$T_J = 125 \text{ °C}$ $V_R = \text{rated } V_{RRM} / V_{DRM}$	5.0				
Typical holding current	Ι <sub>Η</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C	30	mA			
Typical latching current	١L	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	50				
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ , linear to 80 %, $V_{DRM} = R_g - k = open$	150	V/µs			
Maximum rate of rise of turned-on current	dl/dt		100	A/µs			

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>		2.0	vv
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	А
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V
		Anode supply = 6 V, resistive load, $T_J$ = - 65 °C	20	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	15	mA
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	10	
		Anode supply = 6 V, resistive load, $T_J$ = -65 °C	1.2	
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J$ = 25 °C	1	V
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	0.7	V
Maximum DC gate voltage not to trigger	V <sub>GD</sub>	$T_{\rm J} = 125 \ ^{\circ}{\rm C}, \ V_{\rm DRM} = rated \ value \qquad \qquad$		
Maximum DC gate current not to trigger	I <sub>GD</sub>			mA

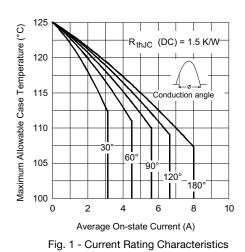
SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	3	μs
Typical turn-off time	tq	1J = 123 C	100	

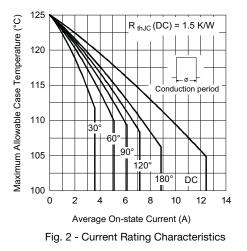
www.vishay.com

VISHAY

## Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C		
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5			
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>		62	°C/W		
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.5			
Approximate weight			2	g		
			0.07	oz.		
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	12TTS	608SH		





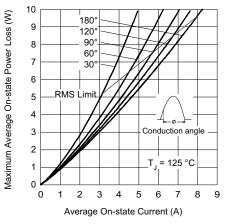


Fig. 3 - On-State Power Loss Characteristics

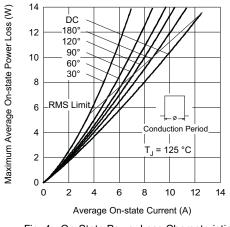
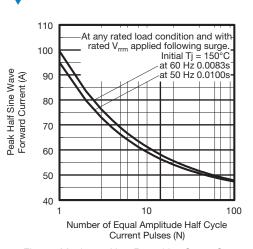


Fig. 4 - On-State Power Loss Characteristics

3	Document Number: 96121
odesAmericas@vishay.com, DiodesA	<u> Asia@vishay.com, DiodesEurope@vishay.com</u>
	DESCRIBED HEREIN AND THIS DOCUMENT
V	• • •

## VS-12TTS08SLHM3

## **Vishay Semiconductors**



www.vishay.com

Fig. 5 - Maximum Non-Repetitive Surge Current

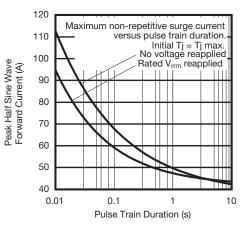


Fig. 6 - Maximum Non-Repetitive Surge Current

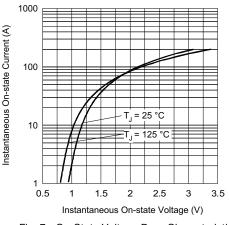


Fig. 7 - On-State Voltage Drop Characteristics

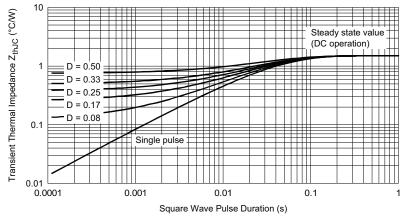


Fig. 8 - Thermal Impedance  $Z_{\text{thJC}}$  Characteristics

## Vishay Semiconductors

**ORDERING INFORMATION TABLE** 

www.vishay.com

ISHA

Device code	VS-	12	т	т	s	08	S	L	н	М3
		2	3	4	5	6	7	8	9	10
	<ol> <li>Vishay Semiconductors product</li> <li>Current rating (12.5 A)</li> <li>Circuit configuration: T = single thyristor</li> <li>Package: T = D<sup>2</sup>PAK (TO-263AB)</li> <li>Type of silicon:</li> </ol>									
	6 - 7 - 8 - 9 - 10 -	Voli S = L = H =	tage rati surface tape an AEC-Q rironmer	101 qua ntal digit	= 800 V) able eft orien alified ::	ted), foi				ontact fa ad (Pb)-f

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-12TTS08SLHM3	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96317				

## **Outline Dimensions**



D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches

www.vishay.com

SHA



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NULES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 08-Jul-15

1



Vishay

## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2024